

## NPN general purpose transistors

## BC846W; BC847W

## FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 65 V).

## APPLICATIONS

- General purpose switching and amplification.

## DESCRIPTION

NPN transistor in a SC70; SOT323 plastic package.  
PNP complements: BC856W and BC857W.

## MARKING

TYPE NUMBER	MARKING CODE <sup>(1)</sup>	TYPE NUMBER	MARKING CODE <sup>(1)</sup>
BC846W	1D*	BC847AW	1E*
BC846AW	1A*	BC847BW	1F*
BC846BW	1B*	BC847CW	1G*
BC847W	1H*		

## Note

- \* = - : Made in Hong Kong.  
\* = t : Made in Malaysia.

## PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector

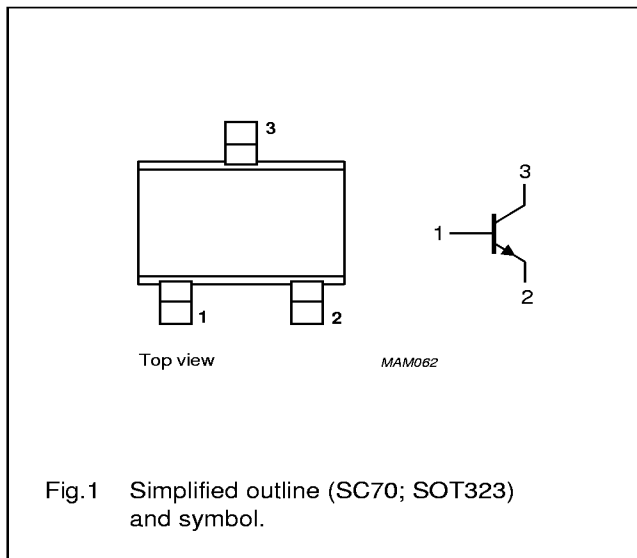


Fig. 1 Simplified outline (SC70; SOT323) and symbol.

## LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter			
	BC846W		–	80	V
	BC847W		–	50	V
$V_{CEO}$	collector-emitter voltage	open base			
	BC846W		–	65	V
	BC847W		–	45	V
$V_{EBO}$	emitter-base voltage	open collector	–	5	V
$I_C$	collector current (DC)		–	100	mA
$I_{CM}$	peak collector current		–	200	mA
$I_{BM}$	peak base current		–	200	mA
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$ ; note 1	–	200	mW
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	junction temperature		–	150	°C
$T_{amb}$	operating ambient temperature		–65	+150	°C

## Note

1. Transistor mounted on an FR4 printed-circuit board.

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## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	625	K/W

## Note

1. Transistor mounted on an FR4 printed-circuit board.

## CHARACTERISTICS

$T_{amb} = 25\text{ °C}$  unless otherwise specified.

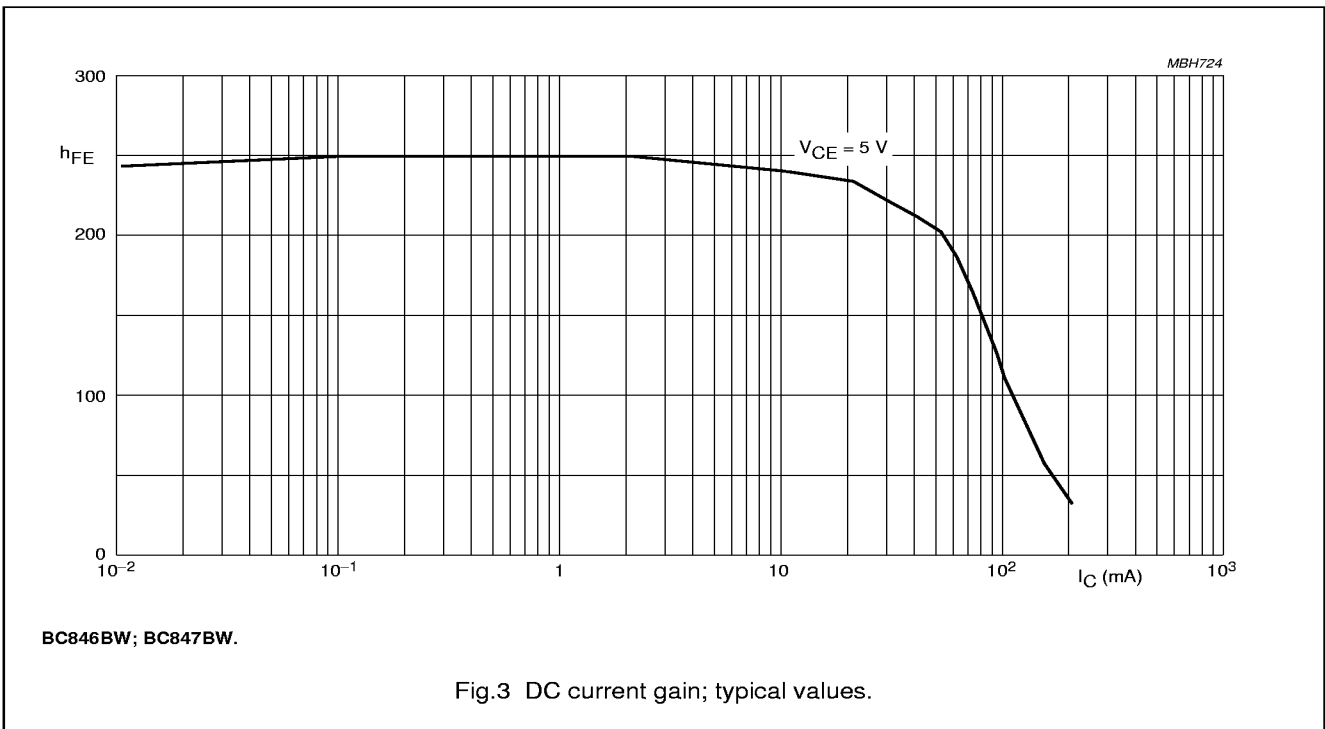
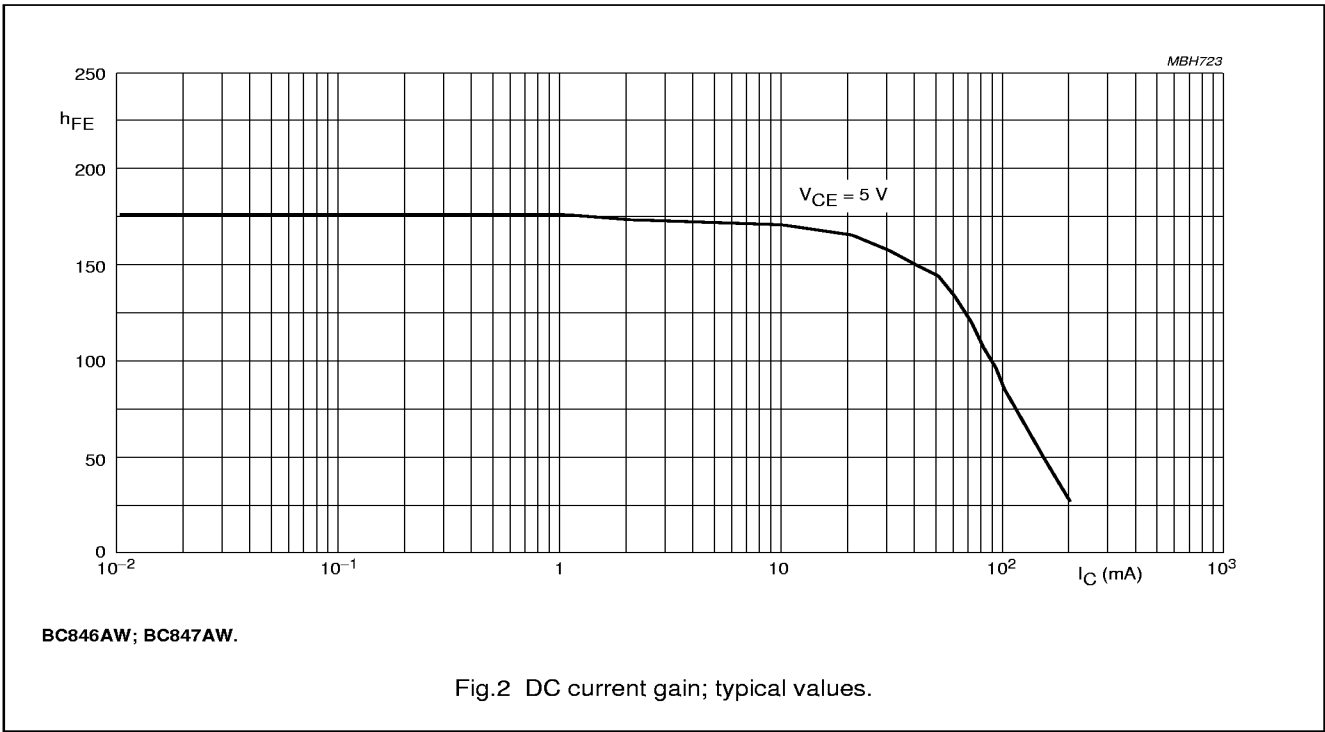
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$I_{CBO}$	collector cut-off current	$I_E = 0; V_{CB} = 30\text{ V}$	–	–	15	nA
		$I_E = 0; V_{CB} = 30\text{ V}; T_j = 150\text{ °C}$	–	–	5	$\mu\text{A}$
$I_{EBO}$	emitter cut-off current	$I_C = 0; V_{EB} = 5\text{ V}$	–	–	100	nA
$h_{FE}$	DC current gain BC846W BC847W BC846AW; BC847AW BC846BW; BC847BW BC847CW	$I_C = 2\text{ mA}; V_{CE} = 5\text{ V};$ see Figs 2, 3 and 4	110	–	450	
			110	–	800	
			110	–	220	
			200	–	450	
			420	–	800	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	–	–	250	mV
		$I_C = 100\text{ mA}; I_B = 5\text{ mA};$ note 1	–	–	600	mV
$V_{BEsat}$	base-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	–	700	–	mV
		$I_C = 100\text{ mA}; I_B = 5\text{ mA}$	–	900	–	mV
$V_{BE}$	base-emitter voltage	$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}$	580	–	700	mV
		$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}$	–	–	770	mV
$C_c$	collector capacitance	$I_E = I_C = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	–	3	pF
$f_T$	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$	100	–	–	MHz
F	noise figure	$I_C = 200\text{ }\mu\text{A}; V_{CE} = 5\text{ V}; R_S = 2\text{ k}\Omega;$ $f = 1\text{ kHz}; B = 200\text{ Hz}$	–	–	10	dB

## Note

1. Pulse test:  $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$ .

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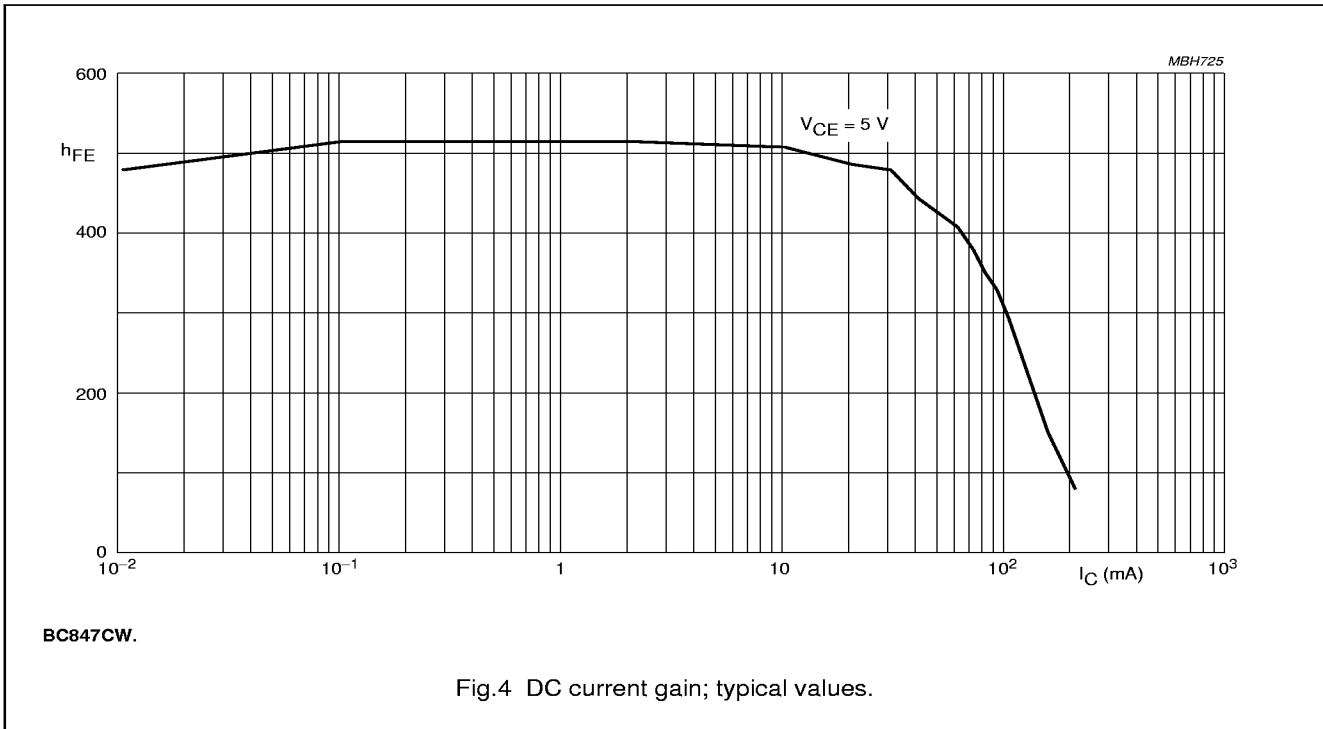


Fig.4 DC current gain; typical values.

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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323

